

Supplementary Information

Preparation and electrochemical performance of porous polymer-derived silicon carbonitride anode by hydrofluoric acid etching for lithium ion batteries

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Supplementary Information List:

Fig.S1 EDX and element content in unetched SiCN (**a**) and SiCN-10-HF materials (**b**).

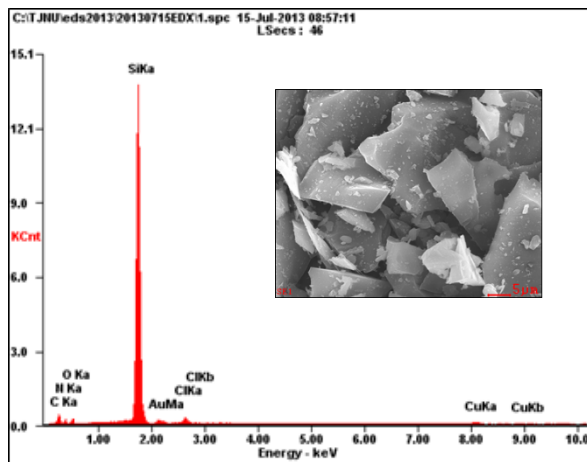
Fig.S2 XPS analysis of survey of unetched SiCN (**a**) and SiCN-10-HF materials (**b**).

Fig.S3 SEM images of the unetched SiCN anode before cycling (**a**) and after 1 (**c**), 10 (**e**), 100 (**g**) cycles; and SiCN-10-HF anode before cycling (**b**), and after 1 (**d**), 10 (**f**), 100 (**h**) cycles.

Tab.S1 Atomic percent of elements on the surface of unetched SiCN and SiCN-10-HF materials determined by XPS analysis.

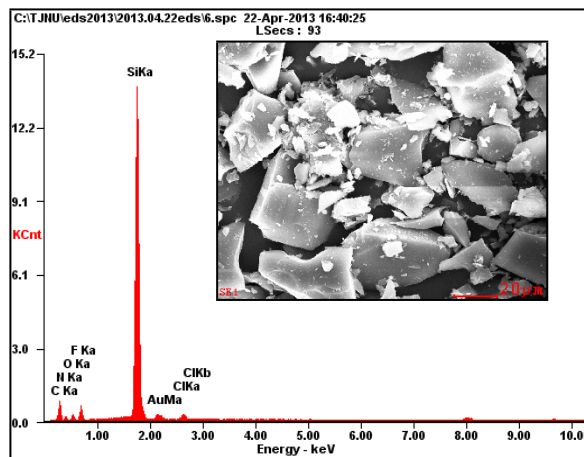
Fig.S1 EDX and element content in unetched SiCN (a) and SiCN-10-HF materials (b).

(a)



<i>Element</i>	<i>Wt%</i>	<i>At%</i>
<i>CK</i>	27.46	42.90
<i>NK</i>	12.35	16.54
<i>OK</i>	05.71	06.70
<i>SiK</i>	48.47	32.38
<i>AuM</i>	03.07	00.29
<i>CIK</i>	01.35	00.72
<i>CuK</i>	01.59	00.47
<i>Matrix</i>	Correction	ZAF

(b)



<i>Element</i>	<i>Wt%</i>	<i>At%</i>
<i>CK</i>	37.02	53.67
<i>NK</i>	07.99	09.94
<i>OK</i>	04.68	05.10
<i>FK</i>	06.90	06.33
<i>SiK</i>	38.97	24.16
<i>AuM</i>	03.42	00.30
<i>CIK</i>	01.01	00.50
<i>Matrix</i>	Correction	ZAF

Fig.S2 XPS analysis of survey of unetched SiCN **(a)** and SiCN-10-HF materials **(b)**.

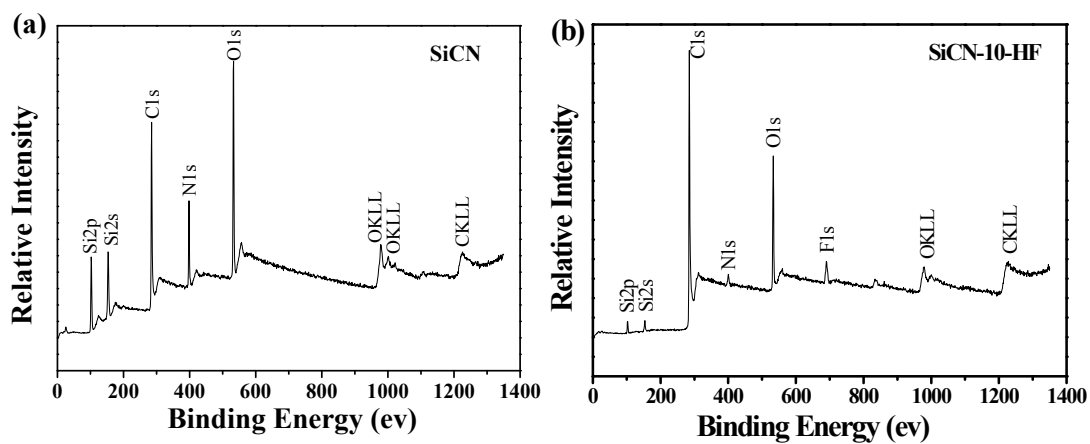
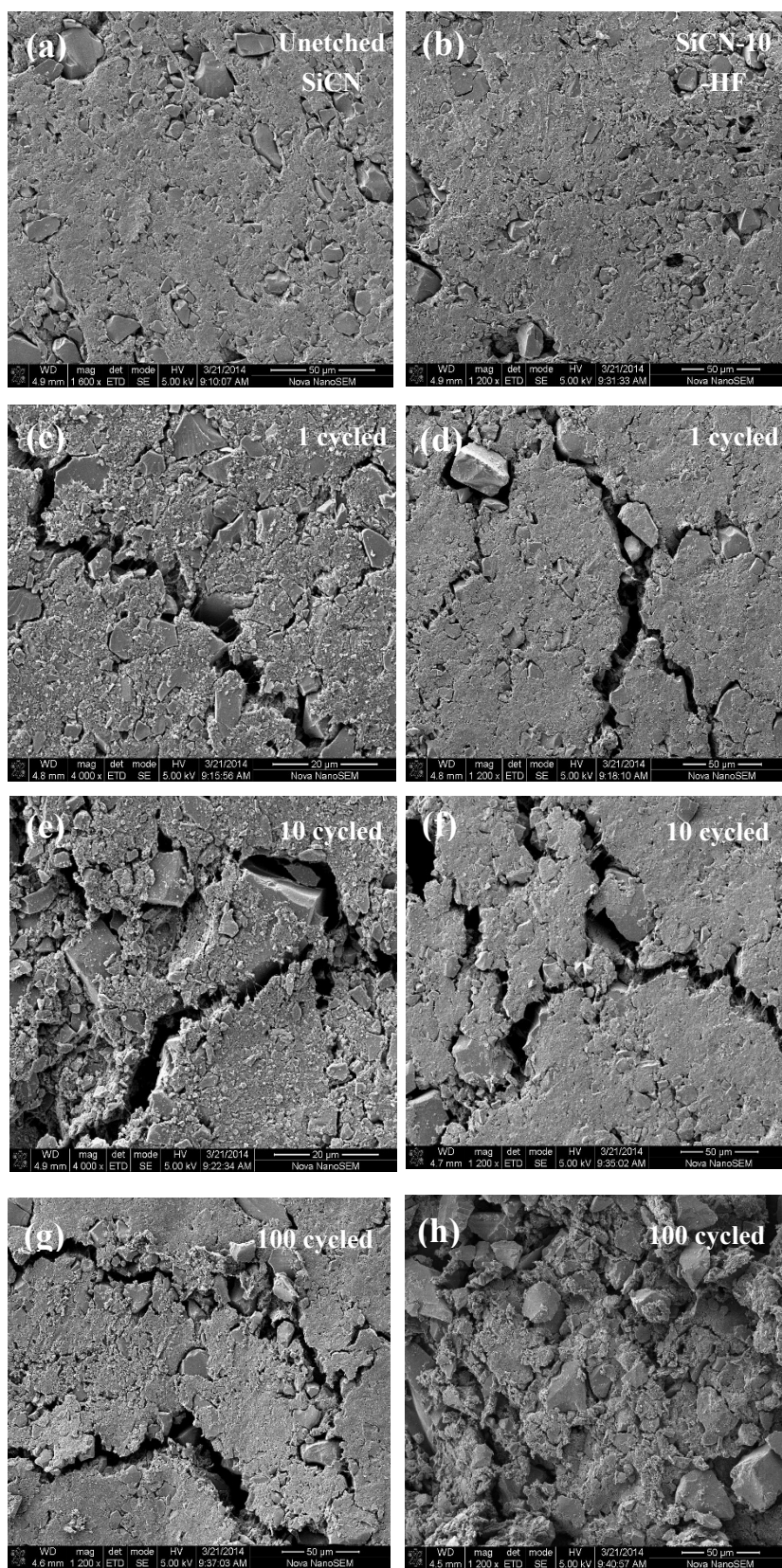


Fig.S3 SEM images of the unetched SiCN anode before cycling **(a)** and after 1 **(c)**, 10 **(e)**, 100 **(g)** cycles; and SiCN-10-HF anode before cycling **(b)**, and after 1 **(d)**, 10 **(f)**, 100 **(h)** cycles.



Tab.S1 Atomic percent of elements on the surface of unetched SiCN and SiCN-10-HF materials determined by XPS analysis.

Sample	In atomic % from XPS				
	Si	C	N	O	F
SiCN	22.13	45.44	11.21	21.22	--
SiCN-10-HF	3.86	74.94	3.74	13.8	3.66